

## Power Schottky rectifier

### Features

- High current capability
- Avalanche rated
- Low forward voltage drop current
- High frequency operation

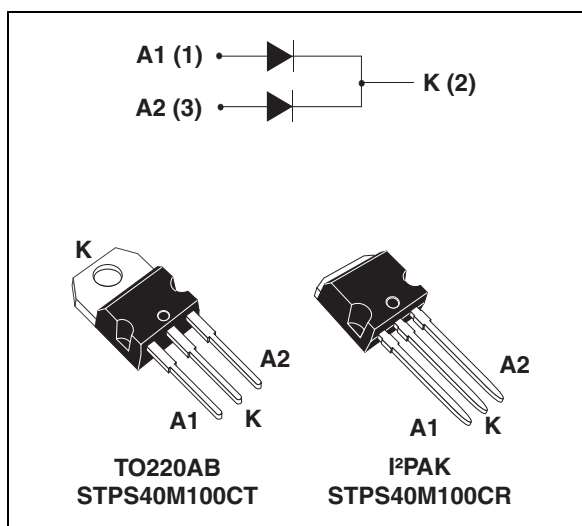
### Description

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

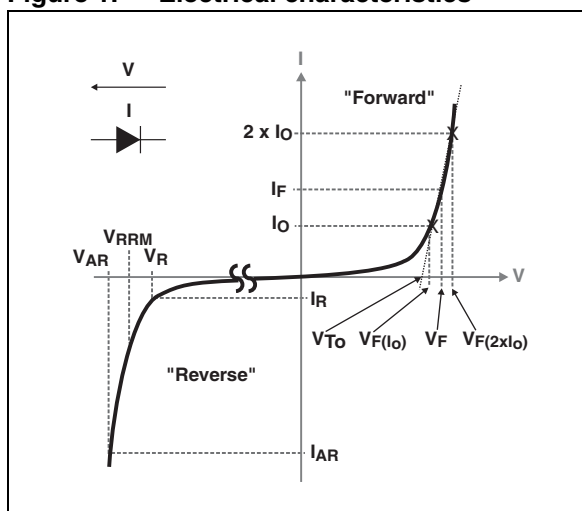
Packaged in TO-220AB and I<sup>2</sup>PAK, this device is intended to be used in notebook, game station and desktop adaptors, providing in these applications a good efficiency at both low and high load.

**Table 1. Device summary**

Symbol	Value
$I_{F(AV)}$	2 x 20 A
$V_{RRM}$	100 V
$T_j$ (max)	150 °C
$V_F$ (typ)	0.420 V



**Figure 1. Electrical characteristics (a)**



- a.  $V_{ARM}$  and  $I_{ARM}$  must respect the reverse safe operating area defined in [Figure 11](#).  $V_{AR}$  and  $I_{AR}$  are pulse measurements ( $t_p < 1 \mu s$ ).  $V_R$ ,  $I_R$ ,  $V_{RRM}$  and  $V_F$  are static characteristics

# 1 Characteristics

**Table 2. Absolute ratings (limiting values per diode at 25 °C unless otherwise stated)**

Symbol	Parameter		Value	Unit	
V <sub>RRM</sub>	Repetitive peak reverse voltage		100	V	
I <sub>F(RMS)</sub>	Forward current rms		60	A	
I <sub>F(AV)</sub>	Average forward current δ = 0.5	T <sub>c</sub> = 125 °C	Per diode	20	A
		T <sub>c</sub> = 120 °C	Per package	40	
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal	530	A	
P <sub>ARM</sub> <sup>(1)</sup>	Repetitive peak avalanche power	t <sub>p</sub> = 1 μs T <sub>j</sub> = 25 °C	23 200	W	
V <sub>ARM</sub> <sup>(2)</sup>	Maximum repetitive peak avalanche voltage	t <sub>p</sub> < 1 μs T <sub>j</sub> < 150 °C, I <sub>AR</sub> < 58 A	120	V	
V <sub>ASM</sub> <sup>(2)</sup>	Maximum single pulse peak avalanche voltage	t <sub>p</sub> < 1 μs T <sub>j</sub> < 150 °C, I <sub>AR</sub> < 58 A	120	V	
T <sub>stg</sub>	Storage temperature range		-65 to + 175	°C	
T <sub>j</sub>	Maximum operating junction temperature <sup>(3)</sup>		150	°C	

1. For temperature or pulse time duration deratings, refer to [Figure 4](#), and [Figure 5](#). More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.
2. Refer to [Figure 11](#)
3.  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  condition to avoid thermal runaway for a diode on its own heatsink

**Table 3. Thermal resistance**

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case	Per diode	1.4	°C/W
		Total	0.95	
R <sub>th(c)</sub>	Coupling		0.5	°C/W

When diodes 1 and 2 are used simultaneously

$$T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

**Table 4. Static electrical characteristics**

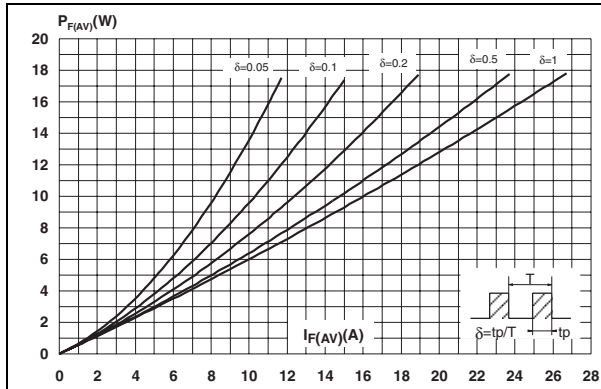
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	-	-	70	μA
		T <sub>j</sub> = 125 °C		-	15	70	mA
		T <sub>j</sub> = 25 °C	V <sub>R</sub> = 70 V	-	-	40	μA
		T <sub>j</sub> = 125 °C		-	7.5	40	mA
V <sub>F</sub> <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 125 °C	I <sub>F</sub> = 5 A	-	0.415	0.500	V
		T <sub>j</sub> = 125 °C	I <sub>F</sub> = 10A	-	0.500	0.560	-
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 20 A	-	-	0.780	-
		T <sub>j</sub> = 125 °C		-	0.585	0.640	-

1. Pulse test: t<sub>p</sub> = 5 ms, δ < 2%
2. Pulse test: t<sub>p</sub> = 380 μs, δ < 2%

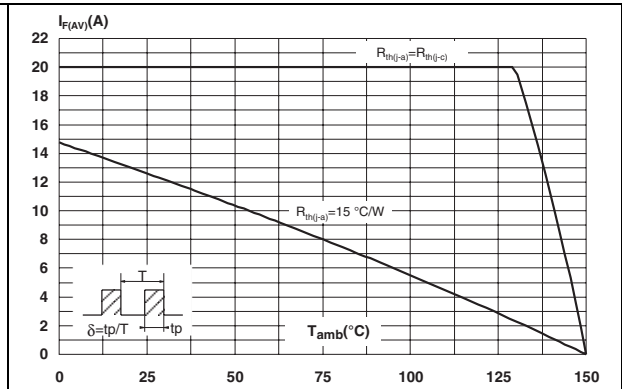
To evaluate the conduction losses use the following equation:

$$P = 0.560 \times I_{F(AV)} + 0.004 \times I_{F(RMS)}^2$$

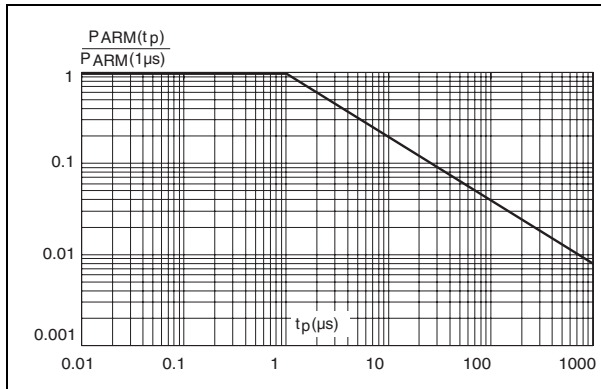
**Figure 2. Average forward power dissipation versus average forward current (per diode)**



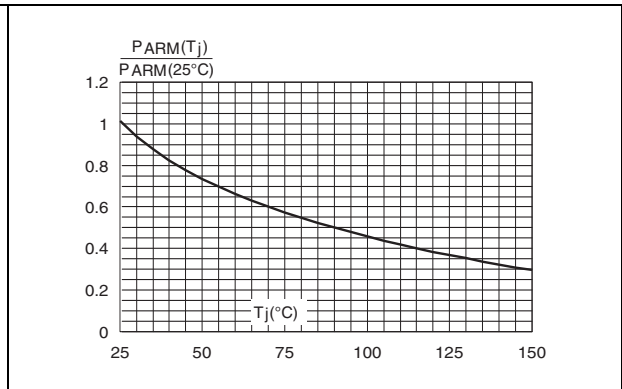
**Figure 3. Average forward current per diode versus ambient temperature ( $\delta = 0.5$ )**



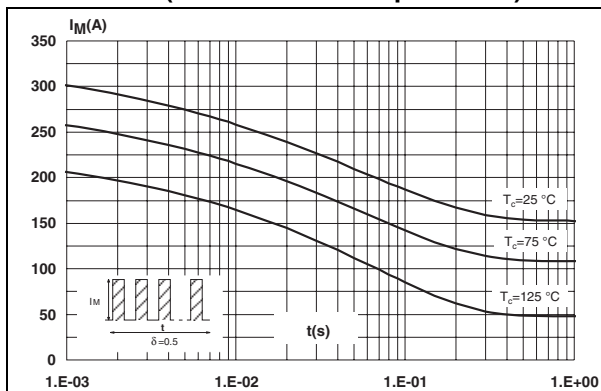
**Figure 4. Normalized avalanche power derating versus pulse duration**



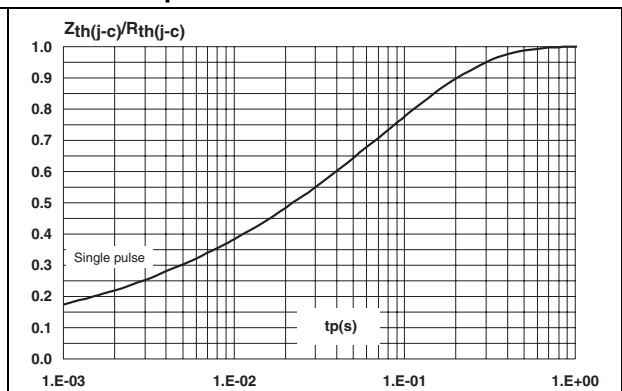
**Figure 5. Normalized avalanche power derating versus junction temperature**



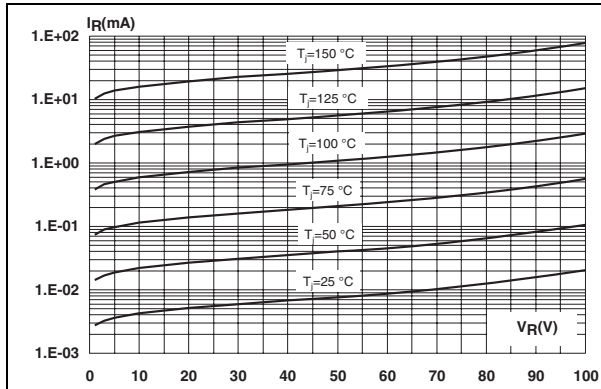
**Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values per diode)**



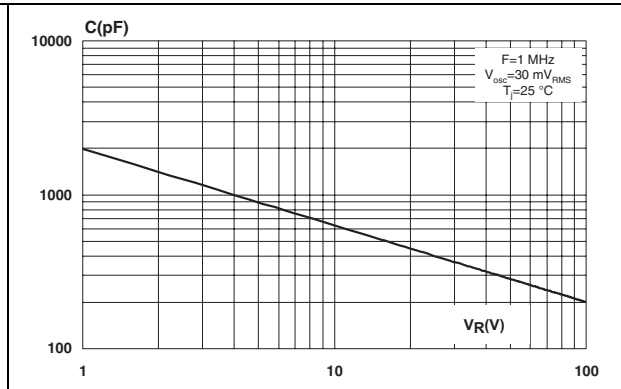
**Figure 7. Relative variation of thermal impedance junction to case versus pulse duration**



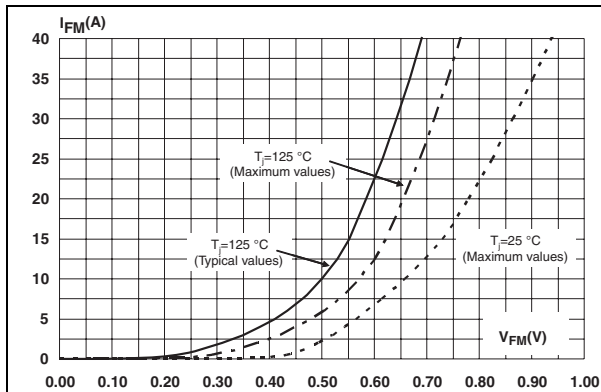
**Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)**



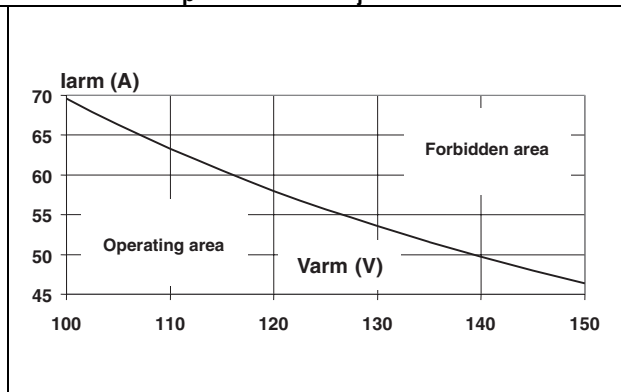
**Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)**



**Figure 10. Forward voltage drop versus forward current (per diode)**



**Figure 11. Reverse safe operating area ( $t_p < 1\ \mu\text{s}$  and  $T_j < 150^\circ\text{C}$ )**



## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: conduction
- Recommended torque value: 0.4 to 0.6 N·m

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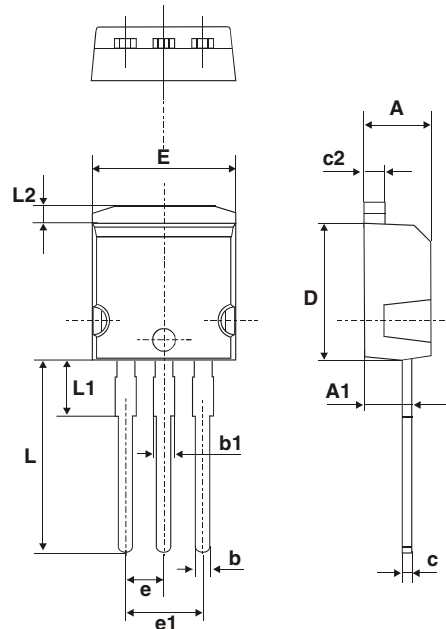
**Table 5. TO-220AB dimensions**

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

Mounting (soldering) the I2PAK metal slug (heatsink) with alloy, like a surface mount device, IS NOT PERMITTED. A standard through-hole mounting is mandatory.

**Table 6. I<sup>2</sup>PAK dimensions**

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055



### 3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS40M100CT	STPS40M100CT	TO-220AB	1.9 g	50	Tube
STPS40M100CR	STPS40M100CR	I <sup>2</sup> PAK	1.5 g	50	Tube

### 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
25-Mar-2009	1	First issue.
10-Apr-2010	2	Updated package graphics.
29-Apr-2010	3	Added I <sup>2</sup> PAK package. Updated weight in <a href="#">Table 7</a> .

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